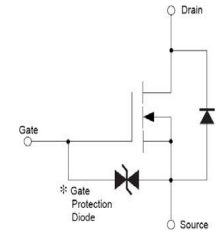




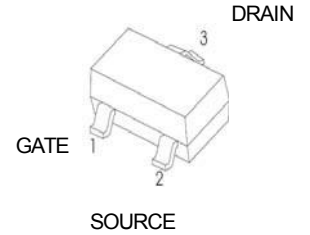
### 2SK3018KT-CAR Plastic-Encapsulate MOSFETS

#### FEATURES

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel



#### Marking: KN



#### MOSFET MAXIMUM RATINGS (T<sub>a</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	0.1	A
P <sub>D</sub>	Power Dissipation	0.15	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	357	°C /W

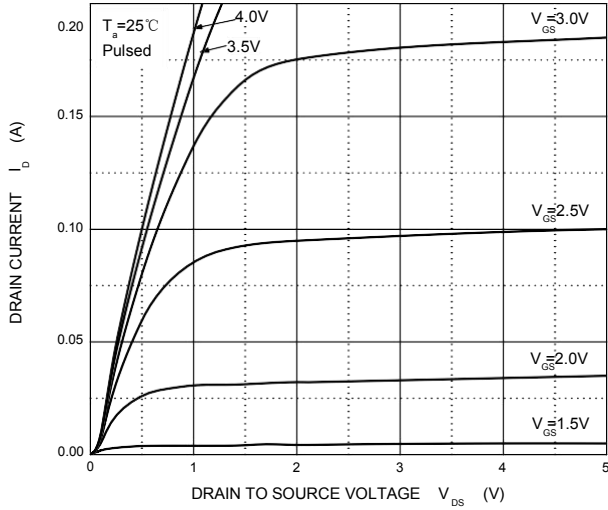
#### MOSFET ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			0.2	μA
Gate -Source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±2	uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 100μA	0.8		1.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4V, I <sub>D</sub> = 10mA			8	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1mA			13	Ω
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	20			mS
<b>Dynamic Characteristics*</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			4		pF
<b>Switching Characteristics*</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 5V, V <sub>DD</sub> = 5V, I <sub>D</sub> = 10mA, R <sub>g</sub> = 10Ω, R <sub>L</sub> = 500Ω,		15		ns
Rise Time	t <sub>r</sub>			35		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			80		ns
Fall Time	t <sub>f</sub>			80		ns

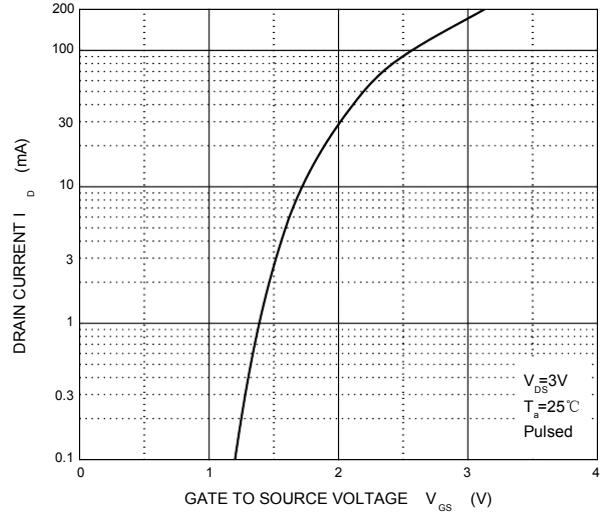


### Typical Characteristics

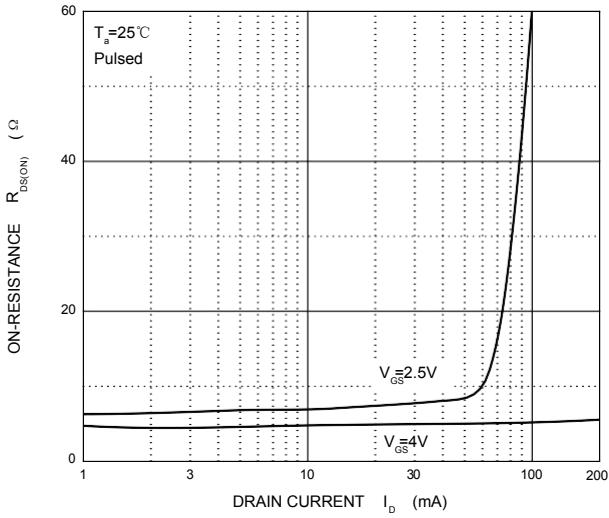
Output Characteristics



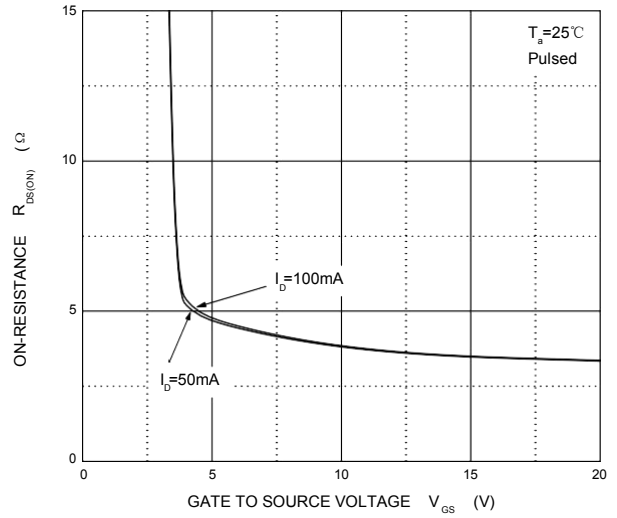
Transfer Characteristics



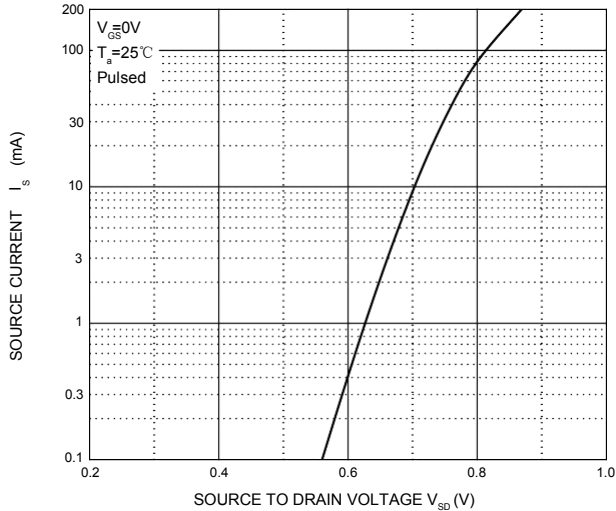
$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$

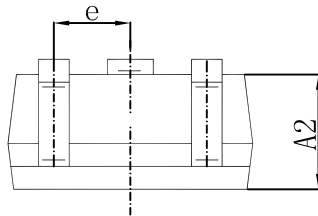
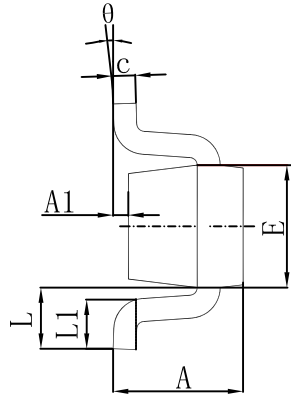
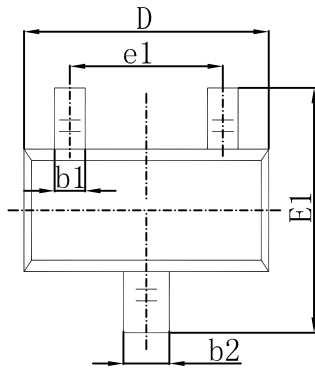


$I_S$  —  $V_{SD}$



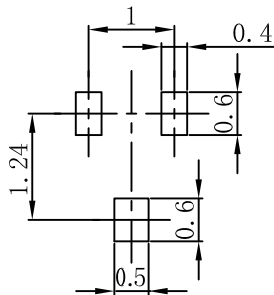


### SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

### SOT-523 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.